

Protection of Lithium-Ion Batteries

Monolithic IC MM1421

Outline

This IC is used to protect single-cell lithium-ion batteries. It adopts an ultra-compact package and has the functions of previous models, with functions for overcharge detection, overdischarge detection and overcurrent detection. A dead time can be set externally.

Features

1. Overcharge detection voltage accuracy (0°C to 50°C) $\pm 25\text{mV/cell}$
2. Consumption current ($V_{\text{cell}}=3.6\text{V}$) 10.0 μA typ.
3. Consumption current ($V_{\text{cell}}=1.9\text{V}$) 0.1 μA typ.
4. Overcharge sensing dead time can be set externally
5. Overdischarge reset reset by charging

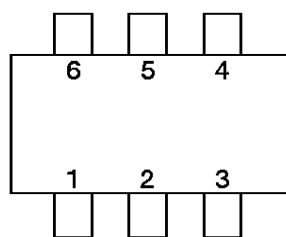
Package

SOT-26A

Applications

IC for protection of single-cell lithium-ion batteries.

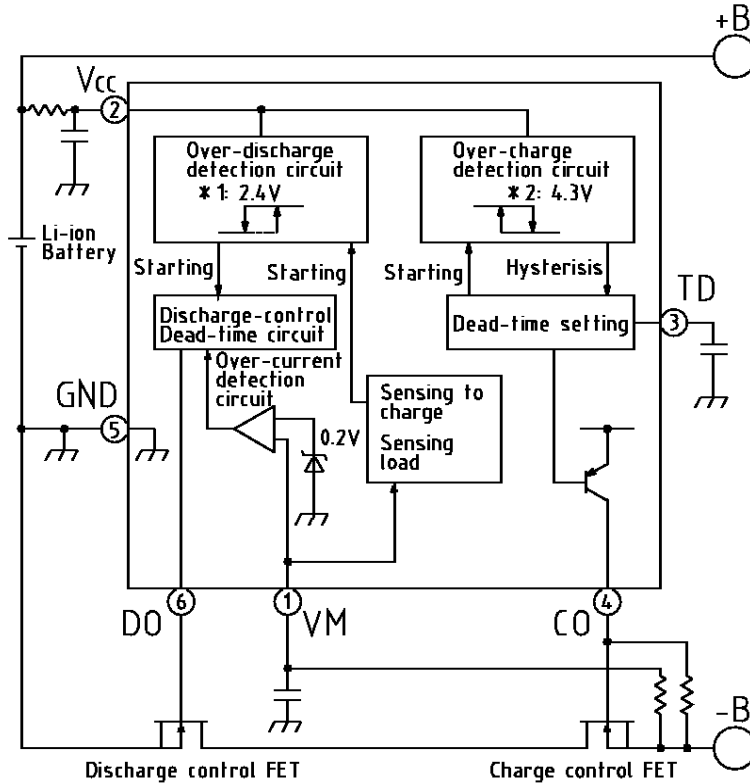
Pin Assignment



SOT-26A

1	VM
2	V _{CC}
3	TD
4	CO
5	GND
6	DO

Block Diagram



Note 1 : Overdischarge voltage
 Note 2 : Overcharge voltage

Pin Description

Pin No.	Pin Name	Function
1	VM	Overcurrent detection input pin. Detects discharge current by connection to charging control FET source pin. Discharge current = (voltage between VM and GND) / (FET × 2 ON resistance)
2	Vcc	Positive power supply pin.
3	TD	Overcharge detection dead time setting pin.
4	CO	Charging control FET (N-ch) gate connection pin. An external resistor (910kΩ) is required between gate and source. Turns off charging control FET (N-ch) for overcharge mode (during charging) and overdischarge mode. Also, overcharge mode (during discharge) turns charging control FET (N-ch) ON, and suppresses FET power consumption.
5	GND	Negative power supply pin. Also, negative input pin for battery connected between Vcc and GND.
6	DO	Discharge control FET (N-ch) gate connection pin. Turns gate OFF for overdischarge mode and overcurrent mode. Turns gate ON for overcharge mode and normal mode.

- (1) Overcharge mode: Battery voltage > overcharge detection voltage
- (2) Normal mode: Overdischarge detection voltage < battery voltage < overcharge detection voltage
 Discharge current < overcurrent detection level
- (3) Overdischarge mode: Overdischarge detection voltage > battery voltage
- (4) Overcurrent mode: Discharge current > overcurrent detection level, voltage between VM and GND = discharge current × FET ON resistance (discharge/charge control FET)

Pin Assignment

Pin No.	Pin name	Equivalent circuit diagram	Pin No.	Pin name	Equivalent circuit diagram
1	V _M		5	GND	
2	V _{CC}		6	DO	
4	CO				
3	TD				

Absolute Maximum Ratings (T_a=25°C)

Item	Symbol	Ratings	Unit
Storage temperature	T _{STG}	-40~+125	°C
Operating temperature	T _{OPR}	-20~+70	°C
Supply voltage	V _{CC} max.	-0.3~+18	V
CO pin voltage	V _{CO} max.	V _{CC} -28~V _{CC}	V
V _M pin voltage	V _{VM} max.	V _{CC} -28~V _{CC}	V
Allowable loss	P _d	200	mW

Recommended Operating Conditions

Item	Symbol	Ratings	Unit
Operating temperature	T _{OPR}	-20~+70	°C
Power supply voltage	V _{OP}	+1.8~+10	V

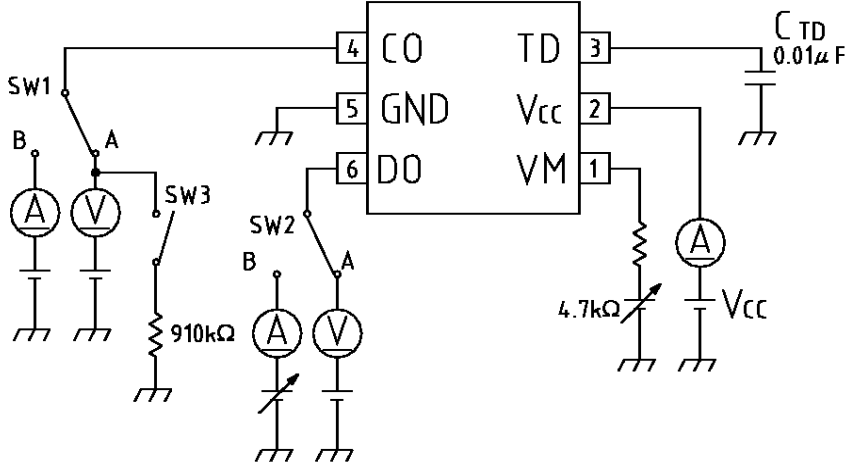
Electrical Characteristics (Except where noted otherwise, Ta=25°C, Vcc=3.6V)

Item	Symbol	Measurement conditions	Min.	Typ.	Max.	Unit
Consumption current 1 (condition: SET)	Icc1	Vcc = 3.6V: Set state between CO-GND: 910kΩ connected		10.0	14.0	uA
Consumption current 2 (condition: IC only)	Icc2	Vcc = 3.6V: IC alone between CO-GND: 910kΩ not connected		6.0	10.0	uA
Consumption current 3 (FET: OFF on SET)	Icc3	Vcc=3.6V: Discharge FET OFF state between CO-GND: 910kΩ not connected				uA
Consumption current 4 (FET: OFF on SET)	Icc4	Vcc=1.9V: Discharge FET OFF state between CO-GND: 910kΩ not connected		0.2	1.0	uA
Consumption current 5 (condition: SET)	Icc5	Vcc=4.5V between CO-GND: 910kΩ connected		35	60	uA
Overcharge detection voltage	VALM1	Ta=0~50°C Vcc: L→H	4.325	4.350	4.375	V
Overcharge hysteresis voltage	VALM1	Vcc: H→L	100	200	300	mV
Overdischarge detection voltage	VALM2	Vcc: H→L	2.30	2.40	2.50	V
Release overdischarge voltage			2.88	3.00	3.12	V
Overcurrent detection level	VVMD	VVM: L→H	174	200	226	mV
Release overcurrent level	VVMDF	VVM: H→L		130		mV
Condition of release overcurrent		Load condition		50		MΩ
Short detection voltage	VVMSHT			1.3		V
Overdischarge detection dead time	tALM2		7.0	10.0	15.0	mS
Overcurrent detection dead time	tVMD	V _M : 0V→0.5V	7.0	10.0	15.0	mS
Short detection delay time	tVMSHT	V _M : 0V→2V		0.02	0.20	mS
Overcharge detection dead time	tALM1	C _{TD} =0.01μF	50	100	150	mS
DO pin output voltage	VGDH	Vcc=3.6V	Vcc-0.3	Vcc-0.1	Vcc	V
DO pin source current 1	IDOH1	V _{DO} =Vcc-1.0V		-100	-30	uA
DO pin source current 2	IDOH2	V _{DO} =Vcc-0.3V		-0.40	-0.70	uA
DO pin sink current 1	IDOL1	V _{VM} >1.0V, V _{DO} =1.0V	50	300		uA
DO pin sink current 2	IDOL2	V _{VM} >1.0V, V _{DO} =0.3V	30	100		uA
DO pin sink current 3	IDOL3	Vcc=3.6V, V _{DO} =1V (Stand-by mode)	1	5		uA
CO pin source current 1	ICo1	V _{CO} =Vcc-1.0V		-20	-10	uA
CO pin source current 2	ICo2	V _{CO} =Vcc-0.3V		-15	-5	uA
CO pin source current 3	ICo3	V _{CO} =Vcc-0.3V (Stand-by mode)				uA
Starting trigger voltage	VST	V _{VM} : 0V→-0.5V	-0.2	-0.1	0	V

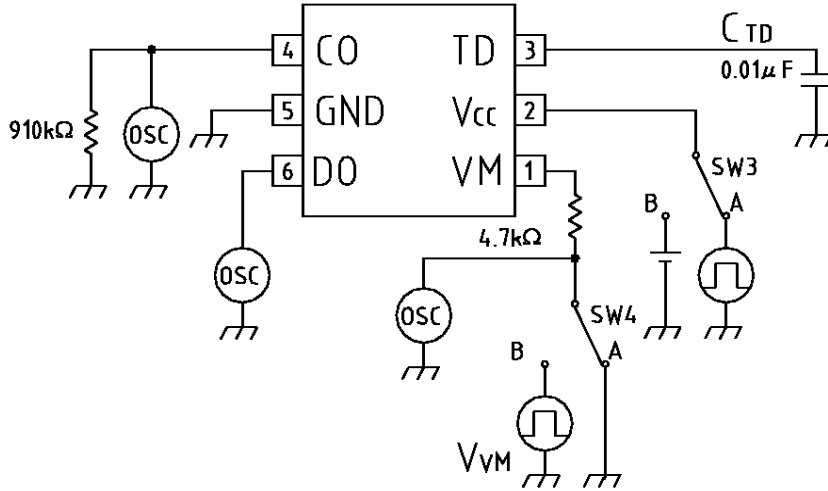
Note: Overcurrent detection current value is V_{VM}/(FET ON resistance×2).

Measuring Circuit

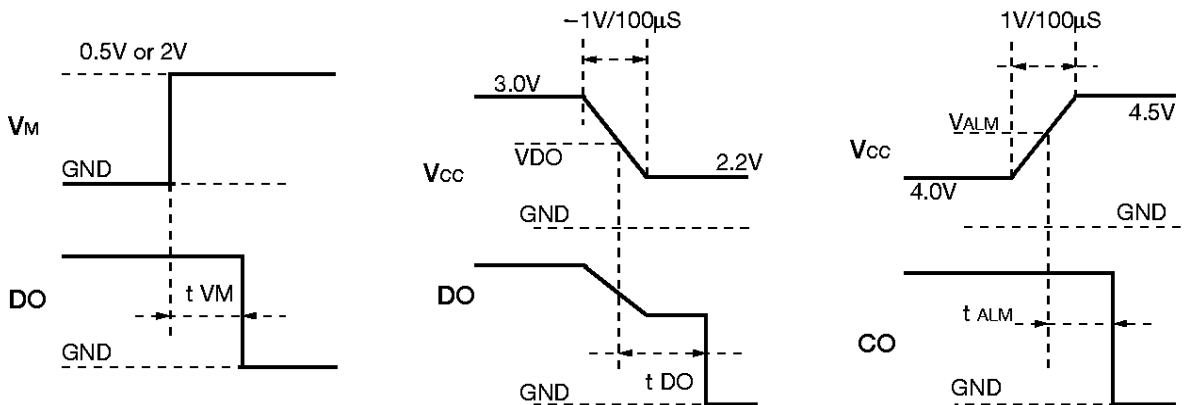
Measuring circuit 1



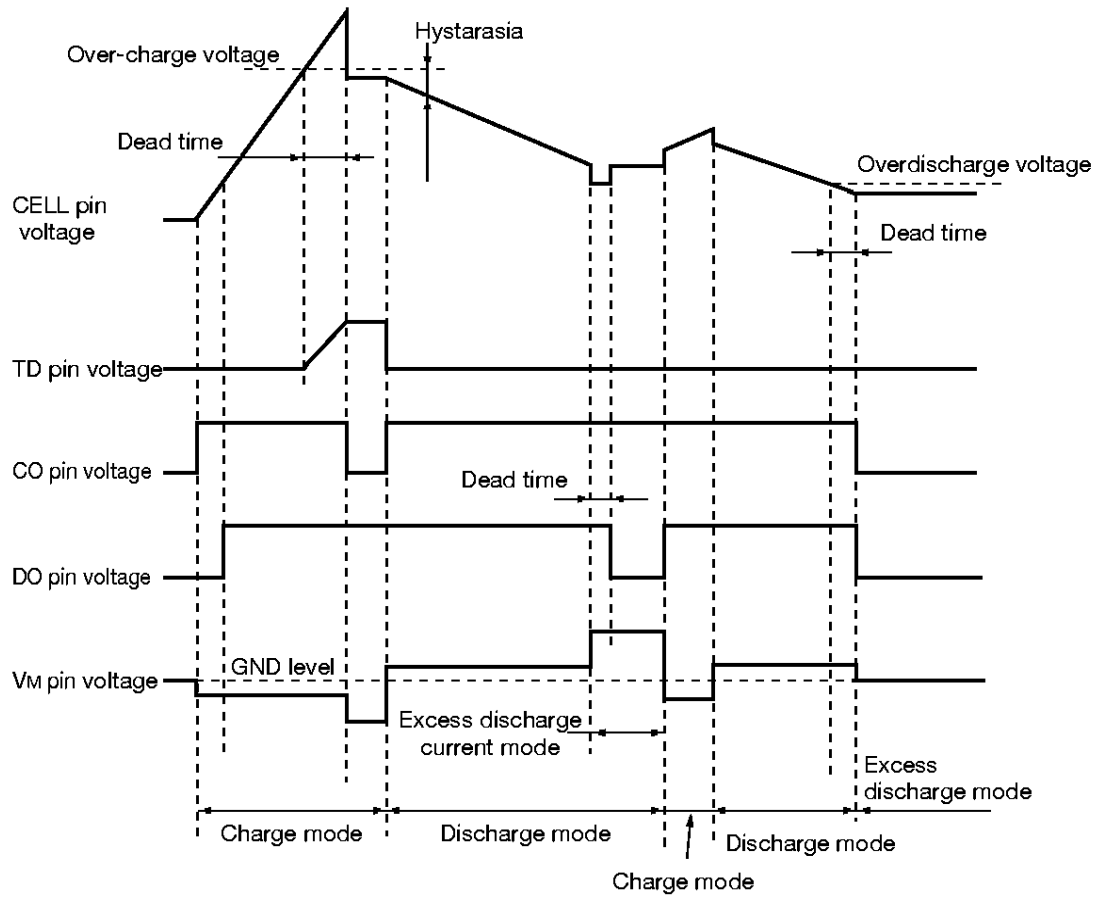
Measuring circuit 2



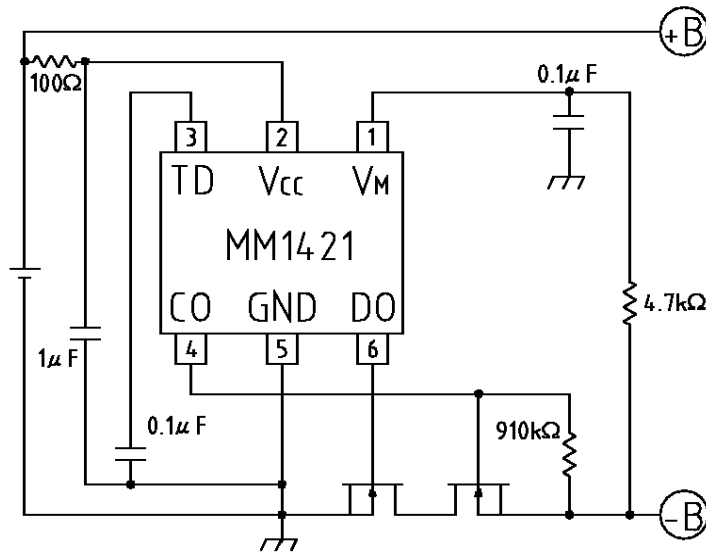
Note :



Timing Chart

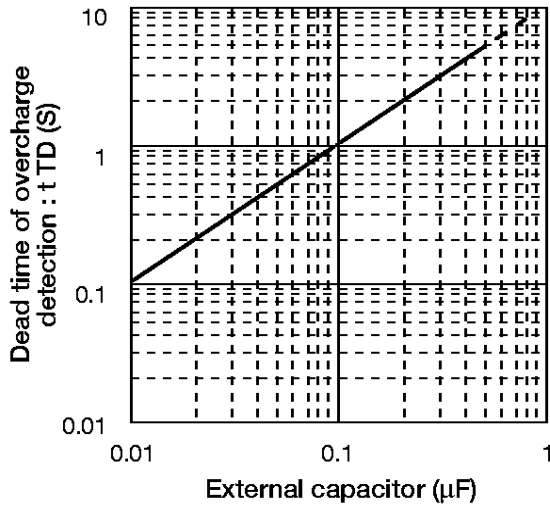


Application Circuit

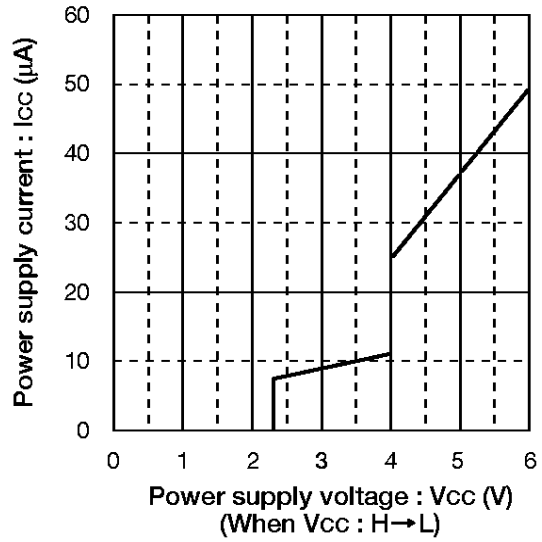


Characteristics

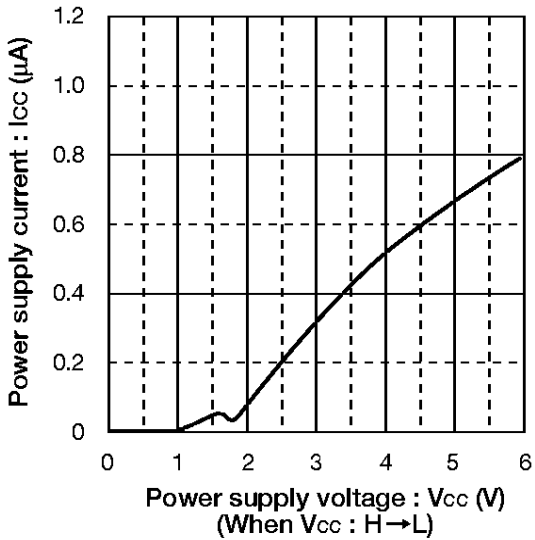
Dead time vs external capacitor
When overcharge detection



Power supply current vs power supply voltage



When stand-by mode
Power supply current vs power supply voltage



DO source current - DO pin voltage
V_{CC}=3.6V

